

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A ~~semiconductor device~~ LED (light-emitting diode device) comprising:

a substrate provided with a region of the back surface having concentrated dislocations at least on part of the back surface thereof;

a semiconductor element layer formed on the front surface of said substrate;

an insulator film formed on said region of the back surface having said concentrated dislocations; and

a back electrode formed to be in contact with a region of the back surface of said substrate other than said region of the back surface having said concentrated dislocations, wherein

the back electrode is a transparent electrode.

2. (Currently Amended) The ~~semiconductor device~~ LED according to claim 1, wherein

said semiconductor element layer is provided with a region of the front surface having said concentrated dislocations at least on part of the front surface thereof,

said semiconductor device further comprising a front electrode formed to be in contact with a region of the front surface of said semiconductor element layer other than said region of the front surface having said concentrated dislocations.

3. (Currently Amended) The ~~semiconductor device~~ LED according to claim 1, wherein

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